



# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · High Breakdown Voltage-
- : V<sub>CBO</sub>= 1500V (Min)
- · High Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

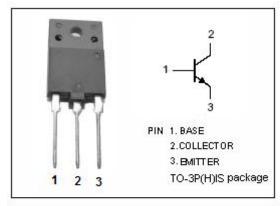
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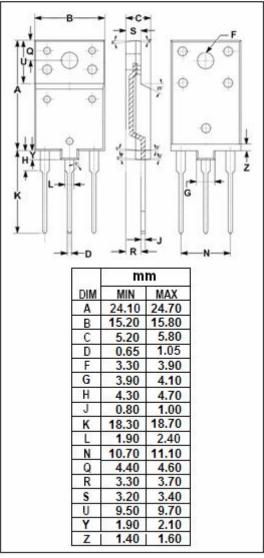
### **APPLICATIONS**

- · Horizontal deflection output for high resolution display.
- High speed switching regulator output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	600	٧	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current- Continuous	10	Α	
Ісм	Collector Current- Peak	20	Α	
I <sub>B</sub>	Base Current	5	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	50	W	
TJ	Junction Temperature	150	${\mathbb C}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	${\mathbb C}$	







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2SC4542

### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.7A			5.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.7A			1.5	V			
V <sub>(BR)</sub> CEO	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; I I <sub>B</sub> = 0	600			V			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 1500V ; I <sub>E</sub> = 0			1.0	mA			
I <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V ; I <sub>C</sub> = 0			10	μ <b>Α</b>			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8						
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V	1	3		MHz			
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f <sub>test</sub> = 1.0MHz		210		pF			
Switching T	ïmes			,					
tstg	Storage Time	I <sub>CP</sub> = 7A , I <sub>B1</sub> = 1.4A; I <sub>B2</sub> = -2.8A;		1.8	2.5	μ <b>S</b>			
t <sub>f</sub>	Fall Time	R <sub>L</sub> = 28.5 Ω		0.1	0.2	μ <b>S</b>			



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